2SA1726

Silicon PNP Epitaxial Planar Transistor (Complement to type 2SC4512)

Application: Audio and General Purpose

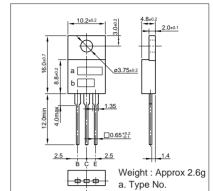
Abso	Absolute maximum ratings (
Syml	loc	2SA1726	Unit		
Vсво		-80	V		
VCEO		-80	V		
VEBO		-6	V		
Ic		-6	A		
lB		-3	А		
Pc		50(Tc=25°C)	W		
Tj		150	°C		
Tstg		-55 to +150	°C		

Electrical C	haracteristics	(Ta=25°C)				
Symbol	Conditions	2SA1726	Unit			
Ісво	Vcb=-80V	-10max	μА			
Гево	VEB=-6V	-10max	μΑ			
V(BR)CEO	Ic=-25mA	-80min	V			
hfe	Vce=-4V, Ic=-2A	50min*				
Vce(sat)	Ic=-2A, IB=-0.2A	-0.5max	V			
fT	Vce=-12V, Ie=0.5A	20typ	MHz			
Сов	VcB=-10V, f=1MHz	150typ	pF			
<u> </u>						

*hfe Rank \(\overline{\text{O}}(50\to 100), P(70\to 140), Y(90\to 180)

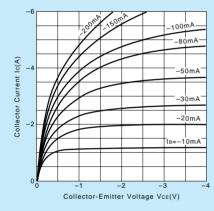
Typical Switching Characteristics (Common Emitter)

	_ · / p									
Ī	Vcc (V)	RL (Ω)	Ic (A)	V _{BB1} (V)	VBB2 (V)	I _{B1} (A)	IB2 (A)	ton (µs)	tstg (µs)	tf (µs)
	-30	10	-3	-10	5	-0.3	0.3	0.18typ	1.10typ	0.21typ

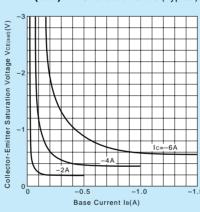


External Dimensions MT-25(TO220)

Ic-VcE Characteristics (Typical)

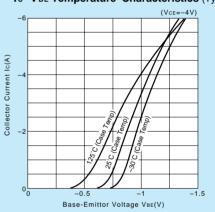


VcE(sat)-IB Characteristics (Typical)

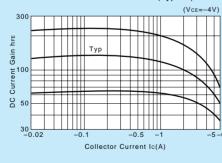


Ic-VBE Temperature Characteristics (Typical)

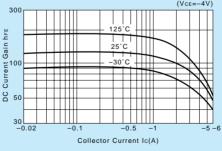
b. Lot No.



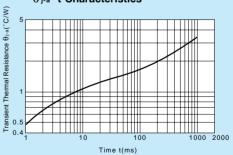
hfe-Ic Characteristics (Typical)



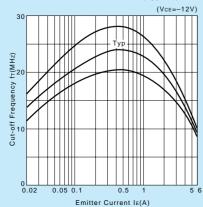
hfe-Ic Temperature Characteristics (Typical)



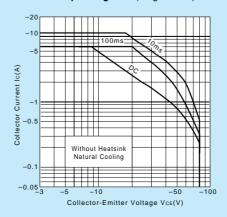
θ_{j-a}-t Characteristics



fT-IE Characteristics (Typical)



Safe Operating Area (Single Pulse)



Pc-Ta Derating

